L Number	Hits	Search Text	DB	Time stamp
1	239	438/42	USPAT	2004/05/12 17:32
2	2109	438/257	USPAT	2004/05/12 17:34
3	809	438/259	USPAT	2004/05/12 17:34
4	548	438/263	USPAT	2004/05/12 17:34
5	733	438/266	USPAT	2004/05/12 17:34
6	480	438/267	USPAT	2004/05/12 17:34
7	929	438/270	USPAT	2004/05/12 17:35
8	471	438/262	USPAT	2004/05/12 17:35
9	1810	438/424	USPAT	2004/05/12 17:35
10	758	438/427	USPAT	2004/05/12 17:35
11	1260	438/700	USPAT	2004/05/12 17:35
12	1472	438/706	USPAT	2004/05/12 17:35
13	410	438/735	USPAT	2004/05/12 17:36
14	1286	438/745	USPAT	2004/05/12 17:36
-	0	10/316908	USPAT	2004/05/12 13:51
-	1	("6236082").PN.	USPAT	2004/05/12 13:51
-	1	("6051465").PN.	USPAT	2004/05/12 13:52
-	1	("6124168").PN.	USPAT	2004/05/12 13:52
-	0	(cell adj transistor) and gate and electrode and floating and source and region and inter-gate and groove and mask and etch and buffer and (etching adj mask)	USPAT	2004/05/12 13:55
-	3	(cell adj transistor) and gate and electrode and floating and source and region and groove and mask and etch and buffer and (etching adj mask)	USPAT	2004/05/12 13:59
-	1	(("6236082").PN.) and (electrode or floating or gate or laminating or laminate or patterning or pattern or substrate or recess or groove or hole or opening or mask or etch or etching or transistor or cell or control or source or region or overlaps or insulating or dielectric or oxide or inter or drain or buffer or spacer or inner or wall or dry or u-shaped or rectangular or deep or depth or width)	USPAT	2004/05/12 17:31
-	1	(("6051465").PN.) and (electrode or floating or gate or laminating or laminate or patterning or pattern or substrate or recess or groove or hole or opening or mask or etch or etching or transistor or cell or control or source or region or overlaps or insulating or dielectric or oxide or inter or drain or buffer or spacer or inner or wall or dry or u-shaped or rectangular or deep or depth or width)	USPAT	2004/05/12 14:09
-	1	(("6124168").PN.) and (electrode or floating or gate or laminating or laminate or patterning or pattern or substrate or recess or groove or hole or opening or mask or etch or etching or transistor or cell or control or source or region or overlaps or insulating or dielectric or oxide or inter or drain or buffer or spacer or inner or wall or dry or u-shaped or rectangular or deep or depth or width)	USPAT	2004/05/12 14:09
-	3	((cell adj transistor) and gate and electrode and floating and source and region and groove and mask and etch and buffer and (etching adj mask)) and (electrode or floating or gate or laminating or laminate or patterning or pattern or substrate or recess or groove or hole or opening or mask or etch or etching or transistor or cell or control or source or region or overlaps or insulating or dielectric or oxide or inter or drain or buffer or spacer or inner or wall or dry or u-shaped or rectangular or deep or depth or width)	USPAT	2004/05/12 14:09

5/12/04